Contents

Preface ix

SECTION I. DEVICES

Surface emitting devices with distributed Bragg reflectors grown by highly precise molecular beam epitaxy
M. Sugimoto, I. Ogura, H. Saito, A. Yasuda, K. Kurihara, H. Kosaka, T. Numai and K. Kasahara 1
1.55 μm buried ridge stripe laser diodes grown by gas molecular beam epitaxy
D. Bonnevie, F. Poingt, L. Le Gouézigou, A. Guichardon, A. Accard, R. Simes, B. Fernier and L. Goldstein 5
Substrate misorientation effects in AlGaInP lasers and crystals grown by gas source molecular beam epitaxy
A. Kikuchi and K. Kishino 9
$In_{0.35}Ga_{0.65}P$ light-emitting diodes grown by gas-source MBE
W.T. Masselink and M. Zachau 14
Enhancements in MBE-grown high-speed GaAs and $In_{0.35}Ga_{0.65}As$ MQW laser structures using binary short-period superlattices
J.D. Ralston, E.C. Larkins, W. Rothemund, I. Esquivias, S. Weisser, J. Rosenzweig and J. Fleissner 19
Parametric investigation of InGaAs/InAlAs HEMTs grown by CBE
G.O. Munns, M.E. Sherwin, Y. Kwon, T. Brock, W.L. Chen, D. Pavlidis and G.I. Haddad 25
Molecular beam epitaxial growth of InAs/GaSb double quantum wells for complementary heterojunction field-effect transistors
K. Yoh, K. Kiyomi, M. Yano and M. Inoue 29
Optimized strained $In_xGa_{1-x}As$ structures for device application
W. Klein, G. Böhm, G. Tränkle and G. Weimann 36
The fabrication of back-gated high electron mobility transistors – a novel approach using MBE regrowth on an in situ ion beam patterned epilayer
E.H. Linfield, G.A.C. Jones, D.A. Ritchie, A.R. Hamilton and N. Iredale 41
Quantum well lasers with InAs monolayers in the active region grown at low temperature by atomic layer molecular beam epitaxy
M.L. Dotor, J. Meléndez, P. Huertas, A. Mazuelas, M. Garriga, D. Golmayo and F. Briones 46
MBE growth of GaAs p–n junction LEDs on (111)A GaAs substrates using only silicon dopant
K. Fujita, A. Shinoda, M. Inai, T. Yamamoto, M. Fujii, D. Lovell, T. Takebe and K. Kobayashi 50
Uniform MBE growth of 2 inch diameter wafer for GaAs/AlGaAs and InGaAs/AlGaAs quantum well lasers
M. Nagai, K. Matsumoto, M. Morishima, H. Horie, Y. Niwata and T. Hayakawa 54
Long term stability of MBE process in MMIC production
Y.C. Pao, J. Franklin and N.G. Bechtel 58
Strain-relaxed, high-speed $In_{0.2}Ga_{0.8}As$ MQW p–i–n photodectors grown by MBE
E.C. Larkins, G. Bender, H. Schneider, J.D. Ralston, J. Wagner, W. Rothemund, B. Dischler, J. Fleissner and P. Koidl 62
Realization of high performance doped-channel MISFETs in highly strained AlGaAs/InGaAs/AlGaAs based quantum wells
K. Kaviani, K. Hu, Q. Xie and A. Madhukar 68
MBE-grown vertical silicon MOSFETs with sub-0.3 μm channel lengths
W. Kiunke, E. Hammerl and I. Eisele 73
Investigation of low temperature (LT) layers of GaAs grown by MBE: comparison of MESFET and HEMT performance
M. Lagadas, K. Tsagaraki, Z. Hatzopoulos and A. Christou 76
High performance MBE of (In)GaAs/AlGaAs heterostructures for HEMTs
G. Böhm, W. Klein, T. Röhr, G. Tränkle, G. Weimann, R.D. Schnell and L. Schleicher 81

SECTION II. GaAs ON Si (AND Ge)

III–V on Si: heteroepitaxy versus lift-off techniques
J. De Boeck and G. Borghs 85

Charged versus neutral interfaces in III–V/Ge quantum wells
L. Sorba, G. Biasiol, G. Bratina, R. Nicolini and A. Franciosi 93
Effects of SiAsBeAs interface structure on the initial stages of GaAs MBE growth on Si(111)
K. Maehashi, S. Hasegawa and H. Nakashima 98
MBE-GaAs on Si, comparison between two GaAs crystal orientations on vicinal Si(100) surface
X.B. Mei, Q. Huang and J.M. Zhou 102
Initial growth process of GaAs on Ge substrate and pseudomorphic Si interlayer
T. Kawai, H. Yonezu, Y. Yamauchi, M. Lopez, K. Pak and W. Kürner 107
GaAs/AlGaAs pin MQW structures grown on patterned Si substrates
K. Woodbridge, P. Barnes, R. Murray, C. Roberts and G. Parry 112
GaInAs/GaAsP buffer layers for low temperature grown GaAs on Si substrates
Y. González, L. González and F. Briones 116
Si–GaAs(001) superlattice structure
L. Sorba, G. Bratina, A. Franciosi, L. Tapfer, G. Scamarcio, V. Spagnolo, A. Migliori, P. Merli and E. Molinari 121

SECTION III. CBE, GSMBE AND ALE

Surface selective growth of GaInAsP heterostructures by metalorganic MBE
H. Heinecke 126
Molecular beam epitaxy of nitride thin films
M.J. Paisley and R.F. Davis 136
MOMBE growth of AlSb and AlGaSb using trimethylamine alane
Y. Okuno, H. Asahi, X.F. Liu, K. Inoue, Y. Itani, K. Asami and S. Gonda 143
Surface morphology of photo-assisted chemical beam epitaxial growth of gallium arsenide
T. Farrell, J.V. Armstrong, T.J. Bullough, R. Beanland, T.B. Joyce and P.J. Goodhew 148
Mechanistic studies of the CBE growth of (100) GaAs using the new precursor tri-isopropylgallium
R.W. Freer, T. Martin, P.A. Lane, C.R. Whitehouse, R. Hogan, J.S. Foord and A.C. Jones 152
Growth of β-$FeSi_2$ on silicon substrates by chemical beam epitaxy
T.E. Crumbaker, J.Y. Natoli, I. Berbezier and J. Derrien 158
Growth investigations of 1.3 μm GaInAsP/InP MQW laser diodes grown by chemical beam epitaxy
H.P. Meier, R.F. Broom, P.W. Epperlein, S. Hausser, A. Jakubowicz and W. Walter 165
Selective area growth of InGaAsP/InP waveguide modulator structures by chemical beam epitaxy
T.H. Chiu, Y. Chen, J. Zucker, J.L. Marshall, S. Shunk and S.N.G. Chu 169
Growth of GaInAs(P)/InP heterostructures on nonplanar substrates using MOMBE (CBE)
B. Baur, H. Heinecke, M. Schier and N. Emeis 175
AlGaAs/GaAs heterostructures for HEMT applications grown by chemical beam epitaxy
H. Rothfritz, R. Müller, G. Tränkle, R. Kempter, J. Plauth and G. Weimann 179
Growth of pseudomorphic $In_xGa_{1-x}As/GaP_yAs_{1-y}$ multiple quantum well structures on GaAs by gas source molecular beam epitaxy
J.E. Cunningham, K.W. Goossen and W. Jan 184
The effects of roughness and composition variation at the InP/InGaAs and InGaAs/InP interfaces on CBE grown quantum wells
A. Antolini, L. Francesio, L. Gastaldi, F. Genova, C. Lamberti, L. Lazzarini, C. Papuzza, C. Rigo and G. Salviati 189
Atomically controlled InGaAs/InP superlattices grown by gas source MEE (migration enhanced epitaxy)
H. Asahi, T. Kohara, R.K. Soni, K. Asami, S. Emura and S. Gonda 194
InP and InAsP/InP heterostructures grown on InP (111)B substrates by gas-source molecular beam epitaxy
H.Q. Hou and C.W. Tu 199
Structural properties of InN films grown on GaAs substrates: observation of the zincblende polytype
S. Strite, D. Chandrasekhar, D.J. Smith, J. Sariel, H. Chen, N. Teraguchi and H. Morkoç 204
Role of growth temperature in GSMBE growth of strained-layer InGaAs/GaAs quantum well lasers
G. Zhang, A. Ovtchinnikov and M. Pessa 209
Layer-by-layer growth mechanism of $Al_xGa_{1-x}P$ grown by gas-source MBE
T. Fujimori, S. Nagao and H. Gotoh 213
Growth of $Ga_{0.29}In_{0.71}As_{0.61}P_{0.39}$ ($\lambda \approx 1.3$ μm) on InP by gas source molecular beam epitaxy
K. Tappura and H. Asonen 217
CBE selective embedded growth for quasi-planar GaAs HBT application
F. Alexandre, D. Zerguine, P. Launay, J.L. Benchimol and J. Etrillard 221

The growth of InAlP using trimethyl amine alane by chemical beam epitaxy
G.O. Munns, W.L. Chen, M.E. Sherwin and G.I. Haddad 226
Facet growth in selective area epitaxy of InP by MOMBE
R. Matz, H. Heinecke, B. Baur, R. Primig and C. Cremer 230
Electrical and optical characterization of semi-insulating $Ga_xIn_{1-x}As_yP_{1-y}$/InP grown by gas source molecular beam epitaxy
Ph. Pagnod-Rossiaux, M. Renaud, F. Gaborit and B. Martin 237
Gas source molecular beam epitaxy of alternated tensile/compressive strained GaInAsP multiple quantum wells emitting at 1.5 μm
J.-Y. Emery, C. Starck, L. Goldstein, A. Ponchet and A. Rocher 241
Growth of InAs/InP and InAsP/InP heterostructures by chemical beam epitaxy
A. Freundlich, A.H. Bensaoula and A. Bensaoula 246
Growth kinetics and in situ composition determination of mixed-group-V compounds grown by gas-source molecular beam epitaxy
C.W. Tu, B.W. Liang and H.Q. Hou 251
Chemical beam epitaxy of $Ga_{0.5}In_{0.5}P$ using tertiarybutylphosphine
J.Ch. Garcia, Ph. Regreny, S.L. Delage, H. Blanck and J.P. Hirtz 255
InGaAs/InP strained layer quantum wells grown by molecular beam epitaxy
S. Loualiche, A. Le Corre, A. Godefroy, F. Clerot, D. Lecrosnier, A. Poudoulec and S. Salaun 258
Electrical properties of P-rich InP grown by gas source MBE
J.Ch. Garcia, J.C. Bourgoin and A. Claverie 261
Beam equivalent pressure measurements in chemical beam epitaxy
T.B. Joyce and T.J. Bullough 265
Study of ALMBE growth conditions for the preparation of compositionally graded AlGaAs/GaAs structures
M. Madella, A. Bosacchi, S. Franchi, P. Allegri and V. Avanzini 270
Characterization of AlAs/GaAs ultrathin-layer superlattices grown by migration enhanced epitaxy at low temperatures
M. Yano, K. Yamamoto, K. Masahara and M. Inoue 274

SECTION IV. II–VI AND IV–VI COMPOUNDS

Recent developments in the MBE growth of wide bandgap II–VI semiconductors for laser diodes and LEDs
J. Qiu, H. Cheng, J.M. DePuydt and M.A. Haase 279
Blue and blue/green laser diodes and LED-based display devices
W. Xie, D.C. Grillo, M. Kobayashi, L. He, R.L. Gunshor, H. Jeon, J. Ding, A.V. Nurmikko, G.C. Hua and N. Otsuka 287
HgCdTe double heterostructure for infrared injection laser
A. Million, T. Colin, P. Ferret, J.P. Zanatta, P. Bouchut, G.L. Destéfanis and J. Bablet 291
CdTe/InSb/α-Sn heterostructures grown by molecular beam epitaxy
N. Libatique, A. Sasaki, D. Choi, S. Wada, A.C. Rastogi, M. Kimata, K. Kaneko and M. Takashima 296
MBE of high mobility PbTe films and PbTe/$Pb_{1-x}Eu_xTe$ heterostructures
G. Springholz, G. Bauer and G. Ihninger 302
Role of the initial growth mode on the dislocation structure in MBE grown ZnSe/GaAs(100)
S. Guha, H. Munekata, L.L. Chang and W.C. Tang 308
Low temperature molecular beam epitaxial growth of ZnS/GaAs(001) by using elemental sulfur source
M. Yoneta, M. Ohishi, H. Saito and T. Hamasaki 314
Indium doping of (001), (111) and (211) CdTe layers grown by molecular beam epitaxy
S. Tatarenko, F. Bassani, K. Saminadayar, R.T. Cox, P.H. Jouneau and N. Magnea 318
Effect of laser on MOMBE of ZnSe using gaseous and solid sources
C.A. Coronado, E. Ho and L.A. Kolodziejski 323
Effects of UV laser irradiation on the growth of nitrogen-doped p-type ZnSe
J. Simpson, S.Y. Wang, I. Hauksson, H. Stewart, S.J.A. Adams, K.A. Prior and B.C. Cavenett 327
Molecular beam epitaxial growth and characterization of (100) HgSe on GaAs
C.R. Becker, L. He, S. Einfeldt, Y.S. Wu, G. Lérondel, H. Heinke, S. Oehling, R.N. Bicknell-Tassius and G. Landwehr 331
High-temperature blue lasing in photopumped ZnSSe–ZnMgSSe double heterostructures
H. Okuyama, Y. Morinaga and K. Akimoto 335
Formation of the ZnTe/(001) GaAs interface
S. Tatarenko, J. Cibert, K. Saminadayar, P.H. Jouneau, V.H. Etgens, M. Sauvage-Simkin and R. Pinchaux 339

Light irradiation effects on impurity doping in ZnSe by photoassisted molecular beam epitaxy
N. Matsumura, K. Senga, Y. Yamashita, S. Ichikawa and J. Saraie 343
MBE growth and characterization of (Zn,Mn)Se/ZnSe and MnSe/ZnSe structures on (001) GaAs
N. Hoffmann, J. Griesche, W. Heimbrodt, O. Goede and K. Jacobs 347
Growth and characterization of CdTe/ZnTe buffer layers on GaAs substrates
L. Parthier, N. Hoffmann, T. Teubner, H. Rossmann, L. Wilde, F. Henneberger and K. Jacobs 352
Effects of ZnSe buffer layer on optical properties of ZnTe grown on GaAs
F. Iida, K. Imai and K. Kumazaki 356
Photoluminescence of ZnSe–ZnTe strained layer superlattices
H. Ozaki, K. Imai and K. Kumazaki 361
Growth and properties of In- and As-doped HgCdTe by MBE
O.K. Wu, D.N. Jamba and G.S. Kamath 365
CdTe/CdMnTe GRINSCH structures for compact lasers in the visible region
G. Feuillet, P.H. Jouneau, J. Cibert, C. Bodin, Le Si Dang, E. Molva and R. Accomo 371
CdHgTe Bragg reflectors grown by molecular beam epitaxy
J. Bleuse, N. Magnea, P.H. Jouneau and H. Mariette 375
Comparison of the p-type dopants K and N in ZnSe
H. Stewart, J. Simpson, S.Y. Wang, I. Hauksson, S.J.A. Adams, K.A. Prior and B.C. Cavenett 379
Undoped and Sb-doped ZnSe-based II–VI superlattices grown by molecular beam epitaxy
A. Shen, L. Xu, H. Wang, Y. Chen, Z. Wang and A.Z. Li 383
ZnSe–GaAs heterojunction parameters
G. Bratina, R. Nicolini, L. Sorba, L. Vanzetti, G. Mula, X. Yu and A. Franciosi 387

SECTION V. Si AND Si/Ge MBE

Effect of surfactants on surface migration in Si MBE
K. Sakamoto, K. Miki, T. Sakamoto, H. Matsuhata and K. Kyoya 392
Surfactant-mediated growth of germanium on Si(100) by MBE and SPE
H.J. Osten, J. Klatt, G. Lippert and E. Bugiel 396
Is low temperature growth the solution to abrupt $Si/Si_{1-x}Ge_x$ interface formation?
S. Fukatsu, N. Usami, K. Fujita, H. Yaguchi, Y. Shiraki and R. Ito 401
Investigation of the growth technique dependence on the optical properties of $Si_{1-x}Ge_x$ alloy layers
V. Arbet-Engels, J.M.G. Tijero, A. Manissadjian, K.L. Wang and V. Higgs 406
Growth and photoluminescence characterization of pseudomorphic SiGe single quantum wells
F. Schäffler, M. Wachter, H.-J. Herzog, K. Thonke and R. Sauer 411
Intersubband absorption in n-type $Si/Si_{1-x}Ge_x$ multiple quantum well structures formed by Sb segregant-assisted growth
K. Fujita, S. Fukatsu, Y. Shiraki, H. Yaguchi and R. Ito 416
High mobility two-dimensional electron gases in $Si/Si_{1-x}Ge_x$ heterostructures grown by MBE
D. Többen, F. Schäffler, M. Besson, C.M. Engelhardt, A. Zrenner, G. Abstreiter and E. Gornik 421
$Si_{1-x-y}Ge_xC_y$ growth and properties of the ternary system
A.R. Powell, K. Eberl, B.A. Ek and S.S. Iyer 425
$Si_{1-x}Ge_x$/sapphire structure fabricated by molecular beam epitaxy
H. Hanafusa, E. Taguchi, H. Ogata and K. Yoneda 430
Cross-sectional scanning tunneling microscopy of MBE-grown Si p–n junctions and Si/SiGe superlattices
E.T. Yu, M.B. Johnson, V.P. Kesan, A.R. Powell, J.-M. Halbout and S.S. Iyer 435
Sn and Sb segregation and their possible use as surfactant for short-period Si/Ge superlattices
W. Dondl, G. Lütjering, W. Wegscheider, J. Wilhelm, R. Schorer and G. Abstreiter 440
Influence of growth conditions on the photoluminescence of pseudomorphic MBE grown $Si_{1-x}Ge_x$ quantum wells
J. Brunner, U. Menczigar, M. Gail, E. Friess and G. Abstreiter 443
Nanometer scale local epitaxy with silicon MBE
E. Hammerl, F. Wittmann, I. Eisele, T. Heinzel, S. Kühn, H. Lorenz and J.P. Kotthaus 447
On optimum design of dislocation filters for reduction of misfit dislocations
K. Maeda, Y. Yamashita, K. Fujita, S. Fukatsu, K. Suzuki, Y. Mera and Y. Shiraki 451
An investigation on the thermal stability of the Ge_xSi_{1-x}/Si superlattice grown by MBE
G. Zhou, X. Zhang, C. Sheng and X. Wang 456
Investigation of surface reconstruction domain behaviour during Si-GSMBE
N. Ohtani, S.M. Mokler, J. Zhang and B.A. Joyce 461

Growth rate dependence on GeH_4 during gas source MBE of Si_xGe_{1-x} alloys grown from Si_2H_6 and GeH_4
S.M. Mokler, N. Ohtani, M.H. Xie, X. Zhang and B.A. Joyce 467
A study of broad band photoluminescence from $Si_{1-x}Ge_x$/Si superlattices
T.D. Steiner, R.L. Hengehold, Y.K. Yeo, D.J. Godbey, P.E. Thompson and G.S. Pomrenke 472
In situ cleaning of Si surfaces by UV/ozone
G. Lippert and H.J. Osten 476
Incorporation and diffusion kinetics during epitaxial growth on Ge(111)
T. Yokotsuka, M.R. Wilby, D.D. Vvedensky, T. Kawamura, K. Fukutani and S. Ino 479
The influence of Cl_2 on $Si_{1-x}Ge_x$ selective epitaxial growth and B-doping properties by UHV-CVD
K. Aketagawa, T. Tatsumi and J. Sakai 484
Intense photoluminescence from strained $Si_{1-x}Ge_x$/Si quantum well structures
S. Fukatsu, N. Usami, H. Yoshida, A. Fujiwara, Y. Takahashi, Y. Shiraki and R. Ito 489

SECTION VI. GROWTH OF III–V COMPOUNDS

As/Ga ratio dependence of Ga adatom incorporation kinetics at steps on vicinal GaAs(001) surfaces
T. Shitara, J. Zhang, J.H. Neave and B.A. Joyce 494
Two-dimensional arsenic-precipitate structures in GaAs
M.R. Melloch, C.L. Chang, N. Otsuka, K. Mahalingam, J.M. Woodall and P.D. Kirchner 499
Determination of the Sb composition profile in MBE-grown GaSb/GaAs structures by high-resolution X-ray diffractometry
O. Brandt, E. Tournié, L. Tapfer and K. Ploog 503
Continuous-space Monte Carlo simulations of epitaxial growth
J. Kew, M.R. Wilby and D.D. Vvedensky 508
Effect of In segregation on the structural and optical properties of ultrathin InAs films in GaAs
O. Brandt, L. Tapfer, K. Ploog, R. Bierwolf and M. Hohenstein 513
Heavily Si or Be doped MBE GaAs grown at low temperatures
S.A. McQuaid, R.C. Newman, M. Missous and S. O'Hagan 515
Low-temperature MBE of AlGaInAs lattice-matched to InP
H. Künzel, J. Böttcher, R. Gibis, H. Hoenow and C. Heedt 519
Desorption mass spectrometric control of composition during MBE growth of AlGaAs
K.R. Evans, R. Kaspi, C.R. Jones, R.E. Sherriff, V. Jogai and D.C. Reynolds 523
Local Mn structures in III–V diluted magnetic semiconductor (In,Mn)As
H. Munekata, L.L. Chang, A. Krol, Y.L. Soo, S. Huang, Z.H. Ming and Y.H. Kao 528

SECTION VII. STRAINED III–V LAYERS

Effects of growth temperature and substrate misorientation in InGaAs/GaAs strained quantum wells grown by MBE
T. Hayakawa, M. Nagai, H. Horie and Y. Niwata 532
Monolayer scale study of segregation effects in InAs/GaAs heterostructures
J.-M. Gérard, C. d'Anterroches and J.-Y. Marzin 536
MBE growth optimization of $In_xGa_{1-x}As$/GaAs multiple quantum well structures
E.C. Larkins, W. Rothemund, M. Maier, Z.M. Wang, J.D. Ralston and W. Jantz 541
Surface segregation of In atoms and its influence on the quantized levels in InGaAs/GaAs quantum wells
K. Muraki, S. Fukatsu, Y. Shiraki and R. Ito 546
Indium surface segregation in strained GaInAs quantum wells grown on GaAs by MBE
J. Nagle, J.P. Landesman, M. Larive, C. Mottet and P. Bois 550
Photoluminescence and X-ray diffraction studies of MBE-grown compressively strained InGaAs and InGaAlAs quantum wells for 1.55 μm laser diode applications
W.-Y. Choi and C.G. Fonstad 555
Non-lattice matched growth of $In_xGa_{1-x}As$ ($0.53 < x < 0.80$) on InP
A. Fischer-Colbrie, R.D. Jacowitz and D.G. Ast 560
The behavior of dopant incorporation and internal strain in $Al_xGa_{1-x}As_{0.03}Sb_{0.97}$ grown by molecular beam epitaxy
A.Z. Li, J.X. Wang, Y.L. Zheng, G.P. Ru, W.G. Bi, Z.X. Chen and N.C. Zhu 566
Transport parameters in pseudomorphic and strain-relaxed InGaAs heterojunctions grown by MBE on misoriented (100) GaAs substrates
J.M. Fernández, J. Chen and H.H. Wieder 570

Temperature dependence of the minimum V/III ratio for the growth of $In_xGa_{1-x}As$
H. Riechert, R. Averbeck and D. Bernklau 575
Optical studies of the growth of single monolayer wide InAs quantum wells on GaAs by MBE
S.S. Dosanjh, P. Dawson, M.R. Fahy, B.A. Joyce, R.A. Stradling and R. Murray 579
Anisotropic relaxation of misfit strain in GaAs films grown on GaP (001)
T. Nomura, K. Ishikawa, K. Murakami and M. Hagino 584
$In_yGa_{1-y}As$/GaAs interface smoothing by GaAs monolayers in highly strained graded superlattice channels ($0.2 \leq y \leq 0.4$) for pseudomorphic $Al_xGa_{1-x}As/In_yGa_{1-y}As$ HFET
J. Kraus, H. Meschede, Q. Liu, W. Prost, F.J. Tegude, H. Lakner and E. Kubalek 589
Microscopic investigation of the strain distribution in InGaAs/GaAs quantum well structures grown by molecular beam epitaxy
M.G. Proietti, F. Martelli, S. Turchini, L. Alagna, M.R. Bruni, T. Prosperi, M.G. Simeone and J. Garcia 592
Structural characterization of highly strained InAs N monolayer lasers and quantum well structures by X-ray diffraction and transmission electron microscopy
A. Mazuelas, S.I. Molina, G. Aragón, J. Meléndez, M.L. Dotor, P. Huertas and F. Briones 596
The growth and physical properties of high quality pseudomorphic $In_xGa_{1-x}As$ HEMT structures
D.R. Mace, M.P. Grimshaw, D.A. Ritchie, A.C. Churchill, M. Pepper and G.A.C. Jones 601
Pseudomorphic InGaAs/GaAs and GaAs/AlGaAs asymmetric triangular quantum wells grown by MBE for optoelectronic device applications
R. Droopad, D.S. Gerber, C. Choi and G.N. Maracas 606
Growth and characterization of AlAs/GaInAs multiple quantum wells
A. Ruiz, C. Giannini, L. Tapfer, K. Ploog, M.I. Alonso, G. Armelles, M. Garriga and P. Castrillo 611
Determination of In composition in molecular beam epitaxy grown $In_xGa_{1-x}As$/GaAs heterostructures
S.M. Wang, E. Olsson, G. Treideris and T.G. Andersson 616
$(Ga_{0.22}In_{0.78}As)_m/(Ga_{0.22}In_{0.78}P)_m$ superlattices grown by atomic-layer molecular beam epitaxy on InP
M.L. Dotor, D. Golmayo and F. Briones 619
Structural and optical characterization of alternately strained GaAs/GaP/GaAs/InP superlattices grown by atomic layer molecular beam epitaxy
A. Mazuelas, J. Meléndez, P.S. Domínguez, M. Garriga, C. Ballesteros, D. Gerthsen and F. Briones 623

SECTION VIII. SILICIDES, METALS AND SUPERCONDUCTORS

Epitaxial growth and homoepitaxy of Pt(110) and Cu(110) on $SrTiO_3$(110)
G.R. Harp, R.F.C. Farrow, R.F. Marks and J.E. Vazquez 627
Structural and electronic properties of pseudomorphic $FeSi_{1+x}$ films on Si(111)
N. Onda, H. Sirringhaus, E. Müller and H. von Känel 634
Epitaxial growth and characterization of lattice-matched $GaAs/Sc_x(Yb,Er)_{1-x}As$/GaAs heterostructures and [$Sc_{0.2}Yb_{0.8}As$, $Sc_{0.3}Er_{0.7}As$] superlattices
A. Guivarc'h, B. Guenais, Y. Ballini, P. Auvray, J. Caulet, M. Minier, G. Dupas, G. Ropars, A. Regreny, R. Guérin and S. Deputier 638
Structural characterization of Nb on sapphire as a buffer layer for MBE growth
P.M. Reimer, H. Zabel, C.P. Flynn and J.A. Dura 643
Pseudo-1D NiAl single-crystal growth on (Al,Ga)As by molecular beam epitaxy
N. Sano, K. Kamigaki, M. Ishida and H. Terauchi 646
MBE growth of ferromagnetic (Mn,Ni)Al thin films on AlAs/GaAs
J.P. Harbison, T. Sands, J. De Boeck, T.L. Cheeks, P. Miceli, M. Tanaka, L.T. Florez, B.J. Wilkens, H.L. Gilchrist and V.G. Keramidas 650
Investigation of MBE-grown high T_c films by RHEED, atomic force microscopy and X-ray diffraction
H.S. Wang, D. Eissler, W. Dietsche, A. Fischer and K. Ploog 655
Application of epitaxial $CoSi_2/Si/CoSi_2$ heterostructures to tunable Schottky-barrier detectors
C. Schwarz, U. Schärer, P. Sutter, R. Stalder, N. Onda and H. von Känel 659
Interaction of molecular beams of KBr with (100) surfaces of KCl
H. Dabringhaus and M. Haag 663
Strain relaxation morphologies of IIa-fluorides and lead-chalcogenide layers on Si(111)
H. Zogg, C. Maissen, S. Blunier, S. Teodoropol, R.M. Overney, T. Richmond and H. Haefke 668
MBE growth of InAs and InSb on $EuBa_2Cu_3O_{7-y}$ superconducting films
Y. Watanabe, F. Maeda, M. Oshima and O. Michikami 672

A strain-relieve transition in epitaxial growth of metals on Si(111) (7 × 7)
T.I.M. Bootsma and T. Hibma 678
Epitaxial growth of Co films and Co/Cu superlattices on sapphire substrates with and without buffer layers
K. Bröhl, P. Bödeker, N. Metoki, A. Stierle and H. Zabel 682

SECTION IX. DOPING OF III–V COMPOUNDS

Properties and applications of carbon-doped GaAs and $Al_xGa_{1-x}As$ layers grown by MBE with a pyrolytic graphite filament
R.J. Malik, J. Nagle, M. Micovic, R.W. Ryan, T. Harris, M. Geva, L.C. Hopkins, J. Vandenberg, R. Hull, R.F. Kopf, Y. Anand and W. Braddock 686
Carbon doping of GaAs for heterojunction bipolar transistors: a comparison between MBE and CBE
J.L. Benchimol, F. Alexandre, N. Jourdan, A.M. Pougnet, R. Mellet, B. Sermage, F. Héliot and C. Dubon-Chevallier 690
Peak-to-valley ratio of 130:1 at 1 K in AlGaAs/GaAs/AlGaAs tunneling structures: evidence for suppressed dopant segregation
J.E. Cunningham, V.J. Goldman, B. Su and W.Y. Jan 695
Electronic properties of multiple Si δ-doped GaAs layers grown by molecular beam epitaxy and migration-enhanced epitaxy
S.M. Shibli, A.B. Henriques, C.A.C. Mendonça, E.C.F. da Silva, E.A. Meneses, L.M.R. Scolfaro and J.R. Leite 700
The impact of lattice dilation on deep states in MBE GaAs
I. Poole, H. Efeoglu, K.E. Singer and A.R. Peaker 703
Erbium complexes and defect levels in MBE-grown erbium-doped GaAs and AlGaAs
D.W. Elsaesser, J.E. Colon, Y.K. Yeo, R.L. Hengehold, K.R. Evans and J.S. Solomon 707
Carbon doping in molecular beam epitaxial (MBE) growth of GaAs using neopentane as a novel carbon source
E. Tokumitsu, M. Shirahama, K. Nagao, S. Nozaki, M. Konagai and K. Takahashi 711
On the potential of δ-doping for AlInAs/GaInAs HEMTs grown by MBE
W. Passenberg, H.-G. Bach, J. Böttcher and H. Künzel 716
Comparison of Si δ-doping with homogeneous doping in GaAs
K. Köhler, P. Ganser and M. Maier 720
Structural and electronic properties of GaAs:C and $Al_xGa_{1-x}As$:C grown by solid-source molecular beam epitaxy
C. Giannini, O. Brandt, A. Fischer, K.H. Ploog and L. Tapfer 724
Electrical properties of MBE grown layers of AlGaAsSb and the effects of proton implantation and hydrogen plasma treatment
A.Y. Polyakov, S.J. Eglash, A.G. Milnes, M. Ye, S.J. Pearton and R.G. Wilson 728
Selective area two-dimensional electron gas structures and in situ ohmic contacts patterned by focused ion beam doping during molecular beam epitaxial growth
J.H. Thompson, G.A.C. Jones, D.A. Ritchie, E.H. Linfield, M. Houlton, G.W. Smith and C.R. Whitehouse 732
The effect of Si planar doping on DX centers in $Al_{0.26}Ga_{0.74}As$
G.S. Solomon, G. Roos and J.S. Harris, Jr. 737

SECTION X. III–V HETEROSTRUCTURES, QUANTUM WELLS AND QUANTUM WIRES

Applications of MBE-grown heterostructures and quantum wells in fundamental research and in advanced semiconductor devices
C. Weisbuch 742
"Quasi-direct" narrow GaSb–AlSb (100) quantum wells
B. Brar, H. Kroemer and J. English 752
Growth studies of (Al,Ga,In)As on InP by molecular beam epitaxy
J.-P. Reithmaier, S. Hausser, H.P. Meier and W. Walter 755
1.3 μm exciton resonances in InGaAs quantum wells grown by molecular beam epitaxy using a slowly graded buffer layer
S.M. Lord, B. Pezeshki, S.D. Kim and J.S. Harris, Jr. 759
Virtual-surfactant epitaxy of InAs quantum wells
E. Tournié, O. Brandt, C. Giannini, K.H. Ploog and M. Hohenstein 765
High mobility and high sheet electron density in selectively doped InAlAs/InGaAs heterostructures grown by MBE on GaAs
T. Mishima, T. Tanimoto, M. Kudoh and M. Takahama 770

Optimization of optical properties of GaAs/GaAlAs quantum wells grown by high temperature migration enhanced epitaxy
F. Laruelle and J. Bloch 774
Molecular beam epitaxial growth of Sb/GaSb multilayer structures: potential application as a narrow bandgap system
T.D. Golding, J.A. Dura, W.C. Wang, J.T. Zborowski, A. Vigliante, H.C. Chen and J.R. Meyer 777
MBE growth and properties of monolayer and submonolayer InAs layer embedded in GaAs/AlAs quantum wells
T. Noda, M.R. Fahy, T. Matsusue, B.A. Joyce and H. Sakaki 783
Surface relaxation kinetics and growth interruption effects in GaAs/AlAs single quantum wells
A. Yoshinaga, P. Mookherjee, R. Murray, J.H. Neave and B.A. Joyce 788
250 Å spacer GaAs–AlGaAs two-dimensional electron gas (2DEG) structures with mobilities in excess of 3×10^6 cm^2 V^{-1} s^{-1} at 4 K
M.C. Holland, A.H. Kean and C.R. Stanley 793
Growth and characterization of Be modulation doped wide parabolic GaAs/$Al_xGa_{1-x}As$ wells
P.F. Hopkins, K.L. Campman and A.C. Gossard 798
Characteristics of in-situ deposited $Si_3N_4/Si/In_{0.53}Ga_{0.47}As$ metal–insulator–semiconductor structures
D.S.L. Mui, A.L. Demirel, S. Strite, Z. Wang, J. Reed, D. Biswas and H. Morkoç 803
Raman scattering analysis of InAs/GaSb ultrathin-layer superlattices grown by molecular beam epitaxy
M. Yano, H. Furuse, Y. Iwai, K. Yoh and M. Inoue 807
Tilted superlattice composition profile measured by photoluminescence and Raman
F.G. Johnson, B.L. Olmsted, S. Chen and G.W. Wicks 812
Structural properties of $Ga_xIn_{1-x}As/Al_yIn_{1-y}As$ multiple layers grown on InP substrates by molecular beam epitaxy
Y.H. Zhang, L. Tapfer, G.H. Lu and K. Ploog 816
Non-equivalence of direct and reverse interfaces in AlAs–GaAs superlattice structures as evidenced by X-ray diffraction
P. Auvray, M. Baudet, C. Deparis and J. Massies 821
Electron distribution and electrical properties of InAs quantum wells
K. Yoh, T. Moriuchi and M. Inoue 826
Growth of ultra-thin AlAs layers on GaAs (001) vicinal surfaces: a search for lateral confinement
B. Chastaingt, C. Deparis, G. Neu, M. Leroux, N. Grandjean and J. Massies 831
Photocurrent and Raman spectroscopy of Stark ladder superlattices with single monolayer AlAs barriers
H. Schneider, J. Wagner, K. Ploog, A. Fischer and K. Fujiwara 836
Substrate temperature dependence of the minority carrier lifetime in (AlGa)As/GaAs MQWs grown with As_2 and As_4
T.S. Cheng, P. Dawson, D.E. Lacklison, C.T. Foxon, J.W. Orton, O.H. Hughes and M. Henini 841
Low temperature (4.2–9 K) transport along InAs–AlSb quantum wells with δ-doped barriers and superconducting niobium electrodes
C. Nguyen, H. Kroemer, E.L. Hu and J.H. English 845

SECTION XI. PATTERNED GROWTH

Cleaved edge overgrowth for quantum wire fabrication
L. Pfeiffer, H.L. Störmer, K.W. Baldwin, K.W. West, A.R. Goñi, A. Pinczuk, R.C. Ashoori, M.M. Dignam and W. Wegscheider 849
Surface structure of high- and low-index GaAs surfaces: direct formation of quantum-dot and quantum-wire structures
R. Nötzel, L. Däweritz and K. Ploog 858
One-step in-situ quantum dots via molecular beam epitaxy
K.C. Rajkumar, K. Kaviani, P. Chen, A. Madhukar, K. Rammohan and D.H. Rich 863
Periodic lateral structure of Al content modulations in AlGaAs grown on vicinal (111)A GaAs by molecular beam epitaxy
T. Yamamoto, M. Inai, T. Takebe, M. Fujii and K. Kobayashi 865
Incorporation of silicon during MBE growth of GaAs on (111)A substrates
M.R. Fahy, J.H. Neave, M.J. Ashwin, R. Murray, R.C. Newman, B.A. Joyce, Y. Kadoya and H. Sakaki 871
Formation of high mobility two-dimensional electron gas at etch-regrown AlGaAs/GaAs interface prepared by chlorine gas etching and MBE in an UHV multichamber system
Y. Kadoya, H. Noge, H. Kano and H. Sakaki 877
Morphology and optical properties of strained InGaAs quantum wires
R. Mirin, M. Krishnamurthy, I.-H. Tan, J.E. Bowers, A.C. Gossard and E.L. Hu 881
MBE regrowth with hydrogen cleaning and its application for the fabrication of surface tunnel transistors
T. Baba, T. Uemura and M. Mizuta 887
Selective InAlAs/InGaAs MBE growth for high frequency OEIC applications
Y.C. Pao, J. Franklin and C. Yuen 892

Selectively masked MBE regrowth
X. Wu, K.H. Gulden, M. Thomas, G. Wilson, J. Walker, G.H. Döhler, J.R. Whinnery and J.S. Smith 896
Formation of multiple quantum wires by strain-induced lateral-layer ordering process
P.J. Pearah, A.C. Chen, A.M. Moy, K.C. Hsieh and K.Y. Cheng 900
Growth of (Al,Ga)As structures on (110)-GaAs by MBE
A.H. Kean, M.C. Holland and C.R. Stanley 904
Observation of quasi-periodic facet formation during high temperature growth of AlAs and AlAs/GaAs superlattices
R. Mirin, M. Krishnamurthy, J. Ibbetson, J. English and A. Gossard 908
The homoepitaxial growth of on-axis GaAs(111)A, (111)B and (201) compared with GaAs(100): doping and growth temperature studies
D.A. Woolf, J.P. Williams, D.I. Westwood, Z. Sobiesierski, J.E. Aubrey and R.H. Williams 913
The molecular beam epitaxial growth of InAs on GaAs(111)B and (100) oriented substrates; a comparative growth study
S.E. Hooper, D.I. Westwood, D.A. Woolf and R.H. Williams 918
Growth kinetics on non-planar substrates
N. Haider, M.R. Wilby and D.D. Vvedensky 922
Growth of [211]-oriented InAs/GaAs heterostructures
M. Ilg, O. Brandt, R. Nötzel and K. Ploog 927
Resharpening effect of AlAs and fabrication of quantum-wires on V-grooved substrates by molecular beam epitaxy
X.Q. Shen, M. Tanaka and T. Nishinaga 932
Study of facet generation during MBE of GaAs on (111)A substrates patterned with ridge-type triangles
T. Takebe, M. Fujii, T. Yamamoto, K. Fujita and K. Kobayashi 937

SECTION XII. MONITORING OF GROWTH, AND EQUIPMENT

Real-time observations of III–V growth on patterned substrates by μ-RHEED
T. Isu, Y. Morishita, S. Goto, Y. Nomura and Y. Katayama 942
RHEED studies of steps, islanding and faceting on singular, vicinal and high-index surfaces
L. Däweritz 949
In-situ microscopy of MBE growth of GaAs and related materials
N. Inoue, M. Tanimoto, K. Kanisawa, S. Hirono, J. Osaka and Y. Homma 956
Scanning tunneling microscopy observation of straight step-edge formation on highly misoriented GaAs (001) surfaces
S. Ohkouchi, I. Tanaka and N. Ikoma 962
Real-time laser-light scattering studies of surface topography development during GaAs MBE growth
G.W. Smith, A.J. Pidduck, C.R. Whitehouse, J.L. Glasper and J. Spowart 966
In-situ doping and composition monitoring for molecular beam epitaxy using mass spectroscopy of recoiled ions (MSRI)
K. Waters, A. Bensaoula, A. Schultz, K. Eipers-Smith and A. Freundlich 972
Phase transition on III–V compound semiconductor surfaces observed by an improved RHEED technique
H. Yamaguchi and Y. Horikoshi 976
High resolution in situ measurement of the surface composition of $In_xGa_{1-x}As$ and $In_xAl_{1-x}As$ at growth temperature
J.-M. Gérard 981
Comparative study of molecular beam injection systems for gas source molecular beam epitaxy
D.A. Scheinowitz, J. Trommel, K. Werner, S. Radelaar and P. Balk 986
Dopant evaporation sources for molecular beam epitaxy
J.F. Walker, M. Micovic, A. Carnera and A. Gasparotto 990
On-site phosphine purification for gas-source MBE of InGaAlP
M.J. Hafich, L.M. Woods, H.S. Kim, G.A. Patrizi and G.Y. Robinson 995
Real-time μ-RHEED observations of droplets on GaAs (111)B surfaces during growth with alternating source supply
Y. Morishita, Y. Nomura, S. Goto, T. Isu and Y. Katayama 999
In situ Auger electron spectroscopy of carbon transient behavior on GaAs surfaces exposed to trimethylgallium
S. Goto, H. Ohno, Y. Nomura, Y. Morishita, A. Watanabe and Y. Katayama 1005
In-situ control of Ga(Al)As MBE layers by pyrometric interferometry
H. Grothe and F.G. Boebel 1010
RHEED and RD monitoring of CBE using TEG and TBA as precursors
G. Paulsson, B. Junno and L. Samuelson 1014
Variation of surface composition during heteroepitaxy observed by coaxial impact collision ion scattering spectroscopy
T. Saitoh, A. Hashimoto, S. Ohkouchi and M. Tamura 1018

RHEED studies of Ga desorption from GaAs and of As desorption from Si-doped GaAs during growth interruption
V. Thierry-Mieg, F. Laruelle and B. Etienne 1022
Simulation of RHEED intensity oscillations during MBE growth
J.P.A. van der Wagt and J.S. Harris, Jr. 1025

SECTION XIII. LATE NEWS

Solubility-limit activation of Si doping at MBE GaAs pn junctions observed by cross-sectional scanning tunneling microscopy
P.D. Kirchner, A. Vaterlaus, R.M. Feenstra, C. Lin, G.D. Pettit and J.M. Woodall 1030
An STM study of molecular-beam epitaxy growth of GaAs
B.G. Orr 1032
GSMBE growth of GaInAsP on GaAs substrates and its application to 0.98 μm lasers
G. Zhang, A. Ovtchinnikov, J. Näppi, T. Hakkarainen and H. Asonen 1033
Selective n- and p-type C-doping in $Ga_{0.47}In_{0.53}As$ superlattices
E.F. Schubert and R.F. Kopf 1037
Formation and photoluminescence of quantum wire structures on vicinal (110) GaAs substrates by MBE
K. Inoue, K. Kimura, K. Maehashi, S. Hasegawa, H. Nakashima, M. Iwane, O. Matsuda and K. Murase 1041
Facetted MBE growth of (GaAl)As on RIE patterned surfaces
M. Walther, T. Röhr, G. Böhm, G. Tränkle and G. Weimann 1045
Self-organization during Si incorporation in MBE-grown vicinal GaAs(001) surfaces
L. Däweritz, K. Hagenstein and P. Schützendübe 1051
RHEED-based measurements of atomic segregation at GaAs/AlAs interfaces
B. Etienne and F. Laruelle 1056
Growth kinetics and critical temperature measurements in MOMBE growth of GaAs with TMGa by RHEED
T. Kaneko, O. Naji, T.S. Jones and B.A. Joyce 1059
Observation of GaAs (001) surfaces at high temperatures by scanning tunneling microscopy
H. Yamaguchi, M. Kasu, T. Sueyoshi, T. Sato and M. Iwatsuki 1064
Mesoscopic step arrays by periodic step bunching on high-index GaAs surfaces
R. Nötzel, D. Eissler and K. Ploog 1068
Direct evidence for native point defects in MBE-grown AlAs/GaAs heterostructures
P. Krispin, R. Hey, H. Kostial and M. Höricke 1073
Atomic-scale view of AlGaAs/GaAs multilayers with cross-sectional scanning tunneling microscopy
M.B. Johnson, U. Maier, H.-P. Meier and H. Salemink 1077
Observation of electroluminescence above room temperature in strained p-type $Si_{0.65}Ge_{0.35}$/Si(111) multiple quantum wells
S. Fukatsu, N. Usami, Y. Shiraki, A. Nishida and K. Nakagawa 1083
Molecular beam epitaxy of precipitation free high temperature $SmBa_2Cu_3O_{7-\delta}$ superconductor thin films with small surface roughness
W. Schindler, P. van Hasselt, P. Tontsch, J. Markl, J. Burger, P. Bauer and G. Saemann-Ischenko 1088

Author index 1091
Subject index 1109